



APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	METHOD OF FORMING A THIN FILM TRANSISTOR BY UTILIZING A LASER CRYSTALLIZATION PROCESS		
Application Type : regular, utility Attorney Docket Number : TOPP0016USA			
Correspondence address: Customer Number: 027765 			
Priority Data: Doc.No: 092116013; Country -TW ; Date: 2003-06-12 us-priority-claimed			
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